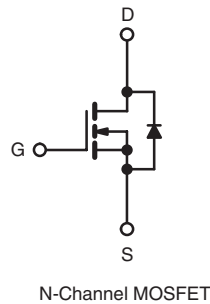
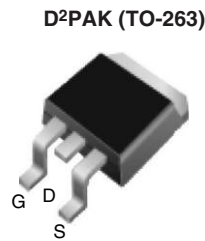


## Power MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	100	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10$ V	0.16
$Q_g$ (Max.) (nC)	26	
$Q_{gs}$ (nC)	5.5	
$Q_{gd}$ (nC)	11	
Configuration	Single	



### FEATURES

- Surface Mount
- Available in Tape and Reel
- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- 175 °C Operating Temperature
- Fast Switching
- Ease of Paralleling
- Lead (Pb)-free Available



Available

**RoHS\***  
 COMPLIANT

### DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The D<sup>2</sup>PAK (TO-263) is a surface mount power package capable of accommodating die size up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D<sup>2</sup>PAK (TO-263) is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0 W in a typical surface mount application.

ORDERING INFORMATION			
Package	D <sup>2</sup> PAK (TO-263)	D <sup>2</sup> PAK (TO-263)	D <sup>2</sup> PAK (TO-263)
Lead (Pb)-free	IRF530SPbF	IRF530STRLPbF <sup>a</sup>	IRF530STRRPbF <sup>a</sup>
	SiHF530S-E3	SiHF530STL-E3 <sup>a</sup>	SiHF530STR-E3 <sup>a</sup>
SnPb	IRF530S	IRF530STRL <sup>a</sup>	IRF530STRR <sup>a</sup>
	SiHF530S	SiHF530STL <sup>a</sup>	SiHF530STR <sup>a</sup>

#### Note

a. See device orientation.

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current	$V_{GS}$ at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	56	W/°C
Linear Derating Factor		0.59	
Linear Derating Factor (PCB Mount) <sup>e</sup>		0.025	
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$	69	mJ
Avalanche Current <sup>a</sup>	$I_{AR}$	14	A
Repetitive Avalanche Energy <sup>a</sup>	$E_{AR}$	8.8	mJ
Maximum Power Dissipation	$P_D$	$T_C = 25$ °C	W
		$T_A = 25$ °C	
Maximum Power Dissipation (PCB Mount) <sup>e</sup>		3.7	
Peak Diode Recovery dV/dt <sup>c</sup>	dV/dt	5.5	V/ns
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature)	for 10 s	300 <sup>d</sup>	

#### Notes

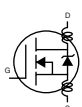

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 25$  V, starting  $T_J = 25$  °C,  $L = 528$   $\mu$ H,  $R_G = 25$   $\Omega$ ,  $I_{AS} = 14$  A (see fig. 12).
- $I_{SD} \leq 14$  A,  $dI/dt \leq 140$  A/ $\mu$ s,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 175$  °C.
- 1.6 mm from case.
- When mounted on 1" square PCB (FR-4 or G-10 material).

\* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Maximum Junction-to-Ambient (PCB Mount) <sup>a</sup>	$R_{thJA}$	-	40	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	1.7	

### Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX. UNIT	
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		100	-	- V	
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$		-	0.12	- V/°C	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0 V	
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100\text{ nA}$	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$		-	-	25 $\mu\text{A}$	
		$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$		-	-	250 $\mu\text{A}$	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 8.4\text{ A}^b$	-	-	0.16 $\Omega$	
Forward Transconductance	$g_{fs}$	$V_{DS} = 50\text{ V}, I_D = 8.4\text{ A}^b$		5.1	-	- S	
<b>Dynamic</b>							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$ , see fig. 5		-	670	-	pF
Output Capacitance	$C_{oss}$			-	250	-	
Reverse Transfer Capacitance	$C_{rss}$			-	60	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}$	$I_D = 14\text{ A}, V_{DS} = 80\text{ V}$ , see fig. 6 and 13 <sup>b</sup>	-	-	26	nC
Gate-Source Charge	$Q_{gs}$			-	-	5.5	
Gate-Drain Charge	$Q_{gd}$			-	-	11	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 50\text{ V}, I_D = 14\text{ A}, R_G = 12\text{ }\Omega, R_D = 3.6\text{ }\Omega$ , see fig. 10 <sup>b</sup>		-	10	-	ns
Rise Time	$t_r$			-	34	-	
Turn-Off Delay Time	$t_{d(off)}$			-	23	-	
Fall Time	$t_f$			-	24	-	
Internal Drain Inductance	$L_D$	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	nH
Internal Source Inductance	$L_S$			-	7.5	-	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p-n junction diode 		-	-	14	A
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$			-	-	56	
Body Diode Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 14\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	2.5	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = 14\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$		-	150	280	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			-	0.85	1.7	$\mu\text{C}$
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )					

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

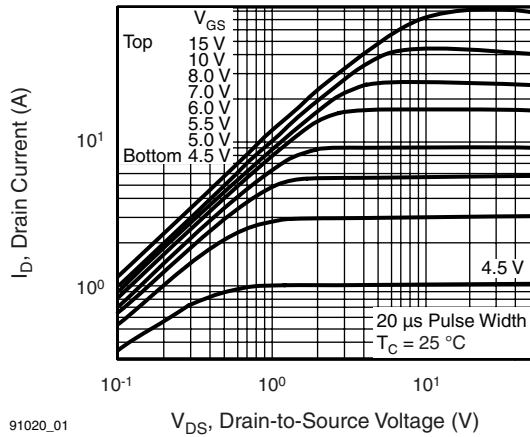


Fig. 1 - Typical Output Characteristics,  $T_C = 25\text{ °C}$

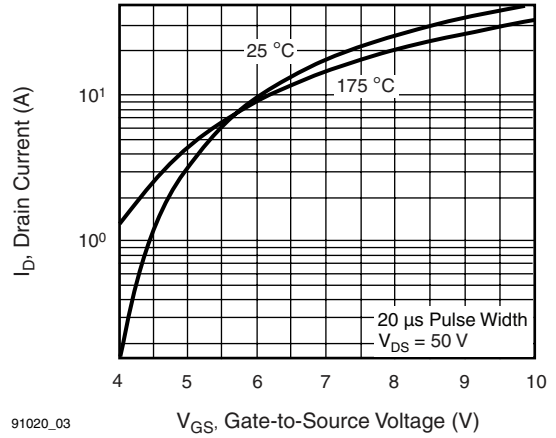


Fig. 3 - Typical Transfer Characteristics

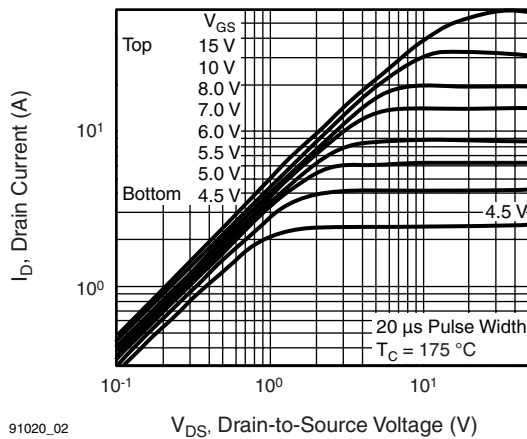


Fig. 2 - Typical Output Characteristics,  $T_C = 175\text{ °C}$

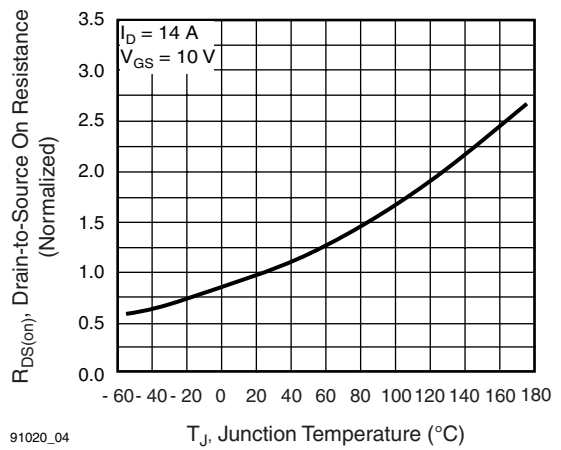
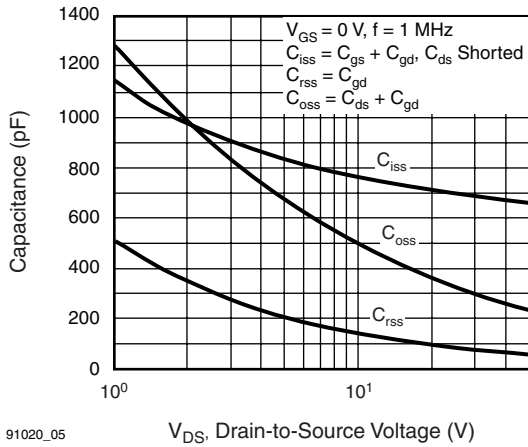
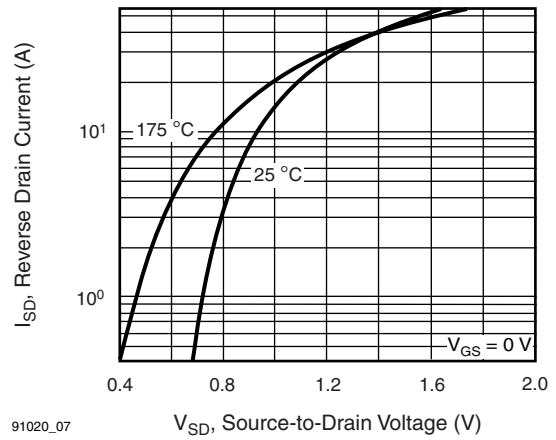


Fig. 4 - Normalized On-Resistance vs. Temperature



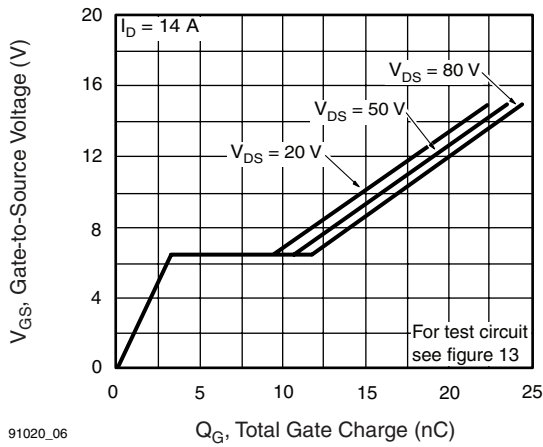
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**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**



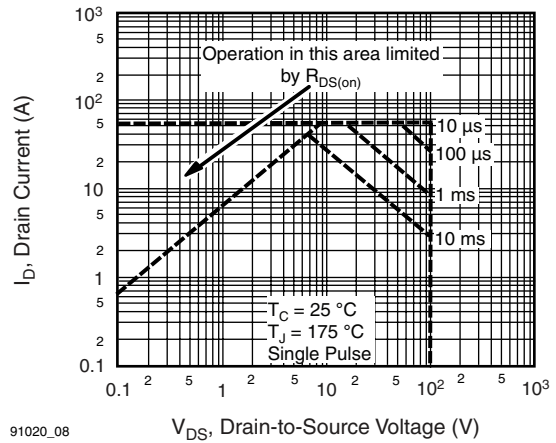
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**Fig. 7 - Typical Source-Drain Diode Forward Voltage**



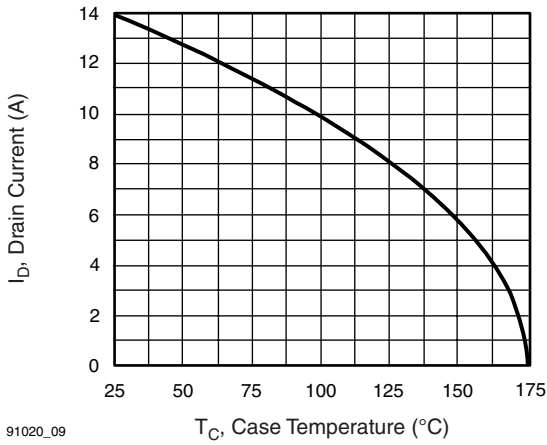
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**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**



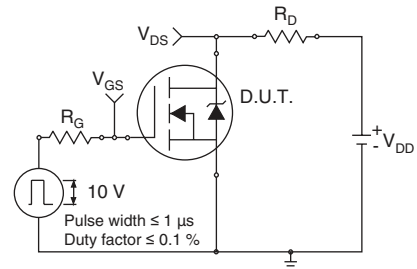
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**Fig. 8 - Maximum Safe Operating Area**

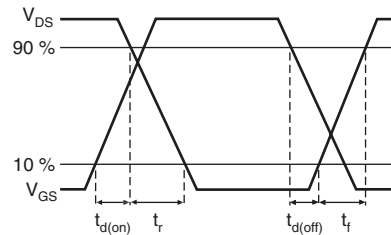


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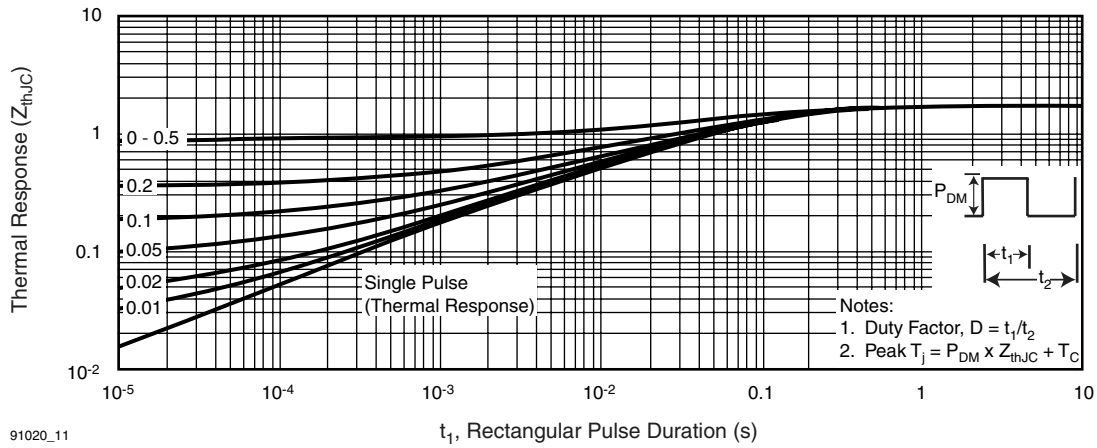
**Fig. 9 - Maximum Drain Current vs. Case Temperature**



**Fig. 10a - Switching Time Test Circuit**



**Fig. 10b - Switching Time Waveforms**



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**Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case**

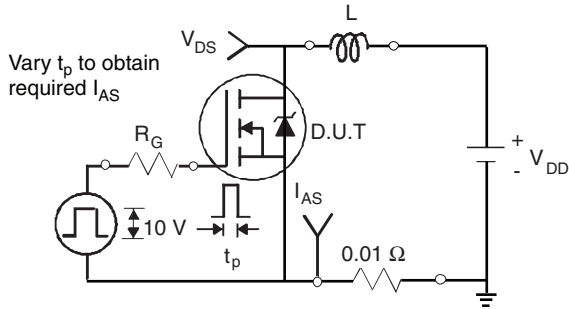


Fig. 12a - Unclamped Inductive Test Circuit

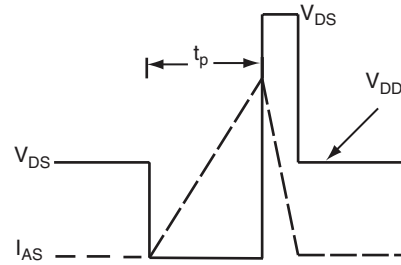


Fig. 12b - Unclamped Inductive Waveforms

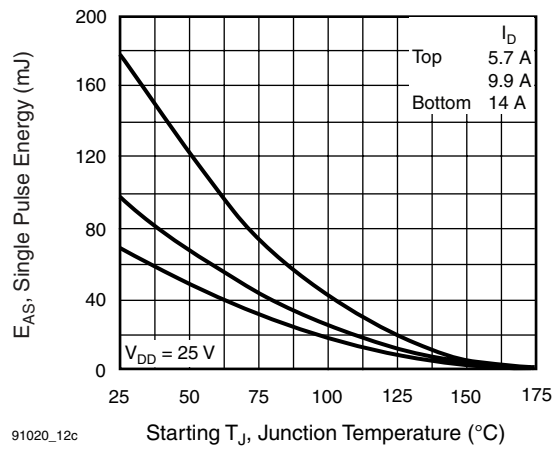


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

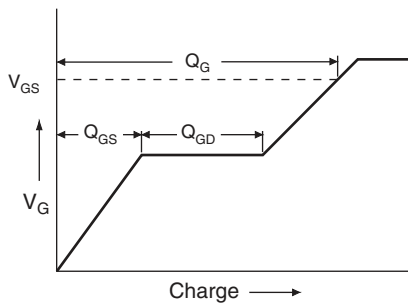


Fig. 13a - Basic Gate Charge Waveform

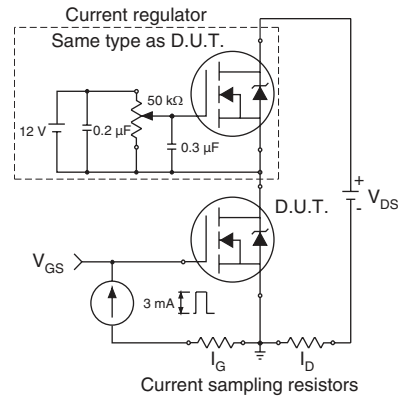
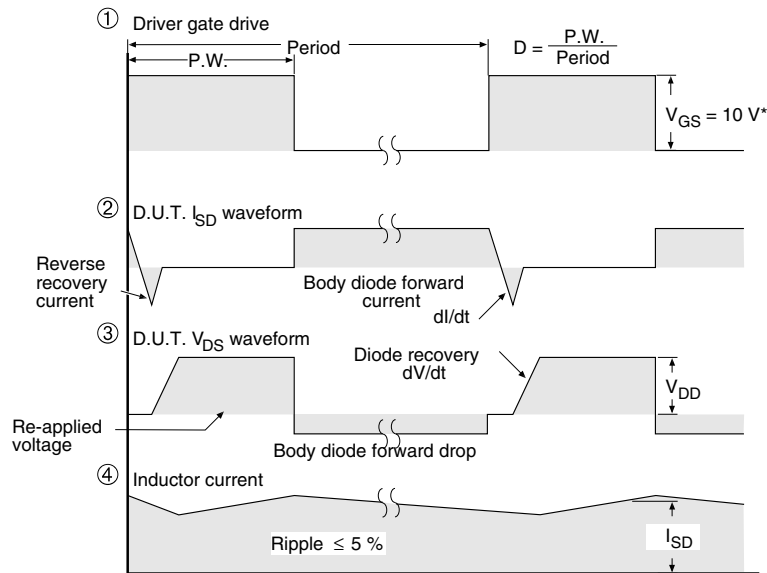
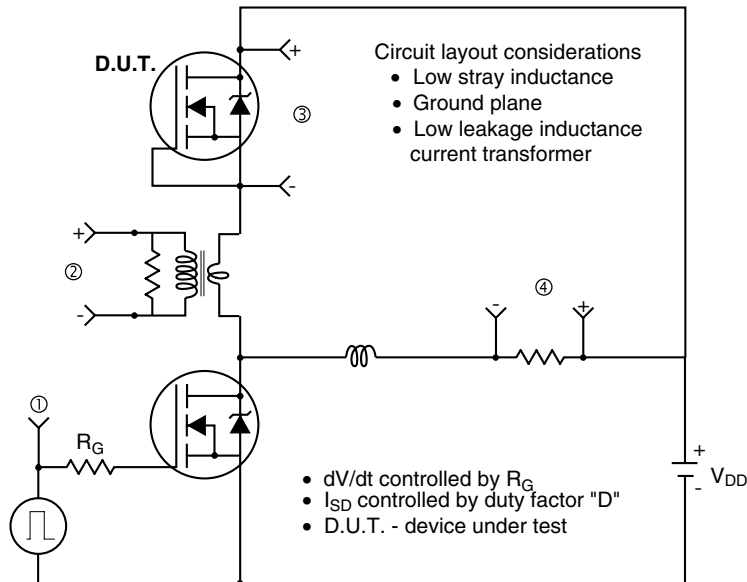


Fig. 13b - Gate Charge Test Circuit

## Peak Diode Recovery $dV/dt$ Test Circuit



\*  $V_{GS} = 5 V$  for logic level and  $3 V$  drive devices

**Fig. 14 - For N-Channel**

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